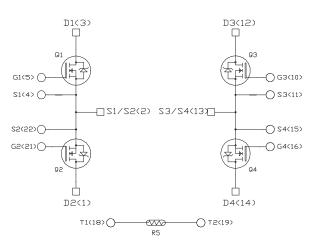
MSCSM120DDUM16TBL3NG

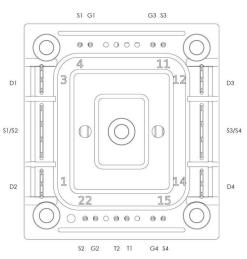
Double Dual Common Source SiC MOSFET Power Module

Product Overview

The MSCSM120DDUM16TBL3NG device is a double dual common source 1200V, 150A silicon carbide (SiC) MOSFET power module.







Note: All ratings at $T_J = 25$ °C, unless otherwise specified.

⚠ CAUTION

These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are the key features of MSCSM120DDUM16TBL3NG device:

- · SiC Power MOSFET
 - High speed switching
 - Low R_{DS(on)}
- · Ultra-low weight and profile
- Kelvin source for easy drive
- Si₃N₄ substrate with thick copper for improved thermal performance
- · Internal thermistor for temperature monitoring
- Extended temperature range

Benefits

The following are the benefits of MSCSM120DDUM16TBL3NG device:

- · High efficiency converter
- · Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- · Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very integrated power conversion system
- Low profile
- RoHS compliant

Application

The following are the applications of MSCSM120DDUM16TBL3NG device:

- · High reliability power systems
- · AC switches

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1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120DDUM16TBL3NG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM120DDUM16TBL3NG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit	
V _{DSS}	Drain-Source voltage	n-Source voltage		V	
I _D	Continuous drain current	Continuous drain current T _H = 25 °C		Α	
	T _H = 80 °C		120		
I _{DM}	Pulsed drain current	drain current			
V _{GS}	Gate-Source voltage	Gate-Source voltage		V	
R _{DS(on)}	Drain-Source ON resistance		16	mΩ	
P _D	Power dissipation	T _H = 25 °C	560	W	

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM120DDUM16TBL3NG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristics	Test Conditions		Min.	Тур.	Max.	Unit
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0V; V _{DS} = 1200V		_	20	200	μΑ
R _{DS(on)}	Drain-Source on	V _{GS} = 20V	T _J = 25 °C	_	12.5	16	mΩ
	resistance	I _D = 80A	T _J = 175 °C	_	20	_	
V _{GS(th)}	Gate threshold voltage	$V_{GS} = V_{DS}$; $I_D = 6 \text{ mA}$		1.8	2.8	_	V
I _{GSS}	Gate–Source leakage current	$V_{GS} = 20V; V_{DS} = 0V$		_	_	200	nA

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM120DDUM16TBL3NG device.

Table 1-3. Dynamic Characteristics

Symbol	Characteristics	Test Conditions		Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	V _{GS} = 0V	V _{GS} = 0V		6040	_	pF
C _{oss}	Output capacitance	V _{DS} = 1000V		_	540	_	
C _{rss}	Reverse transfer capacitance	f = 1 MHz		_	50	_	
Q_g	Total gate charge	V _{GS} = -5V/20V		_	464	_	nC
Q _{gs}	Gate-Source charge	V _{Bus} = 800V		_	82	_	
Q _{gd}	Gate-Drain charge	I _D = 80A		_	100	_	
T _{d(on)}	Turn-on delay time	V _{GS} = -5V/20V		_	30	_	ns
Tr	Rise time	V _{Bus} = 600V		_	30	_	
T _{d(off)}	Turn-off delay time	I _D = 100A		_	50	_	
T _f	Fall time	$R_{G(on)} = 4\Omega$ $R_{G(off)} = 2.4\Omega$			25	_	
E _{on}	Turn-on energy	V _{GS} = -5V/20V	T _J = 150 °C	_	2.4	_	mJ
E _{off}	Turn-off energy	$V_{Bus} = 600V$ $I_{D} = 100A$ $R_{G(on)} = 4\Omega$ $R_{G(off)} = 2.4\Omega$		_	1.3	_	
R _{Gint}	Internal gate resistance			_	1.94	_	Ω
R _{thJH}	Junction-to-heatsink the	ermal resistance	$\lambda = 3.4 \text{ W/mK}$	_	0.268	_	°C/W

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM120DDUM16TBL3NG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristics	Test Conditions	Min.	Тур.	Max.	Unit
V_{SD}	Diode forward voltage	$V_{GS} = 0V; I_{SD} = 80A$	_	4	_	V
		$V_{GS} = -5V; I_{SD} = 80A$	_	4.2	_	
t _{rr}	Reverse recovery time	$I_{SD} = 80A; V_{GS} = -5V$	_	90	_	ns
Q _{rr}	Reverse recovery charge	$V_R = 800V$; $di_F/dt = 2000 A/\mu s$	_	1100	_	nC
Irr	Reverse recovery current		_	27	_	Α

1.2 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120DDUM16TBL3NG device.

Table 1-5. Thermal and Package Characteristics

Symbol	Characteristics			Min.	Тур.	Max.	Unit
V _{ISOL}	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz			2500	_	_	V
T _J	Operating junction temperature r	ange		- 55	_	175	°C
T_JOP	Recommended junction temperature under switching conditions			- 55	_	T _{Jmax} –25	
T _{STG}	Storage case temperature			- 55	_	125	
T _C	Operating case temperature			- 55	_	125	
Torque	Mounting torque To heatsink M3			0.7	_	0.9	N.m
Wt	Package weight			_	32.5	_	g

The following table lists the temperature sensor NTC of the MSCSM120DDUM16TBL3NG device.

Table 1-6. Temperature Sensor NTC

Symbol	Characteristics		Min.	Тур.	Max.	Unit
R ₂₅	Resistance at 25 °C		_	50	_	kΩ
$\Delta R_{25} / R_{25}$	_		_	5	_	%
B _{25/85}	T ₂₅ = 298.15K		_	3952	_	K
ΔΒ/Β	_	T _C = 100 °C	_	4	_	%

$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$
 R_T: Thermistor value at T

Note: See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

1.3 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM120DDUM16TBL3NG device.

Figure 1-1. Junction-to-Heatsink Thermal Impedance

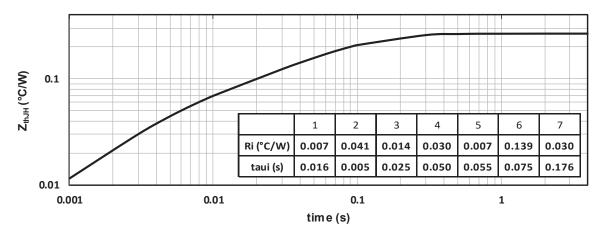


Figure 1-2. Output Characteristics, $T_J = 25$ °C

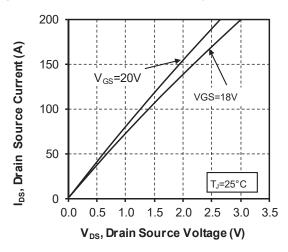


Figure 1-3. Output Characteristics, T_J = 175 °C

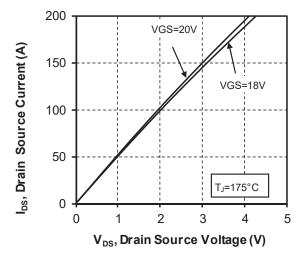


Figure 1-4. Normalized R_{DS(on)} vs. Temperature

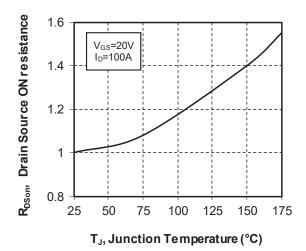


Figure 1-5. Transfer Characteristics

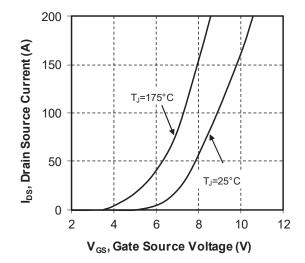


Figure 1-6. Switching Energy vs. Rg

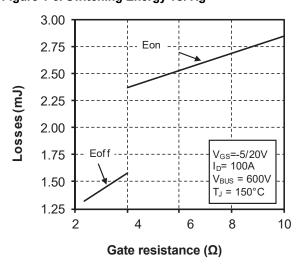


Figure 1-7. Switching Energy vs. Current

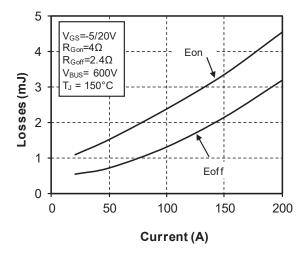


Figure 1-8. Capacitance vs. Drain Source Voltage

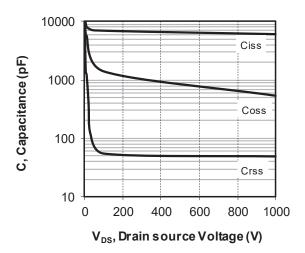


Figure 1-9. Gate Charge vs. Gate Source Voltage

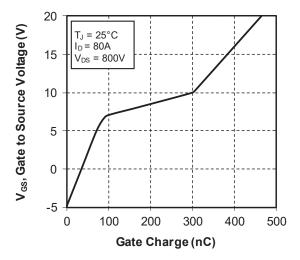


Figure 1-10. Body Diode Characteristics, T_J = 25 °C

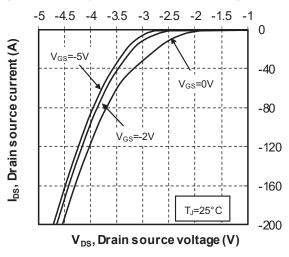


Figure 1-11. 3rd Quadrant Characteristics, T_J = 25 °C

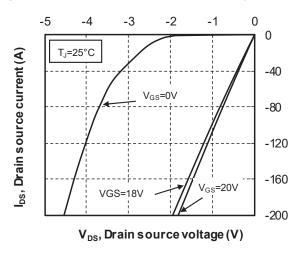
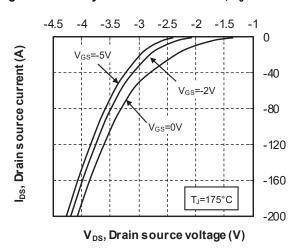


Figure 1-12. Body Diode Characteristics, T_J = 175 °C Figure 1-13. 3rd Quadrant Characteristics, T_J = 175 °C



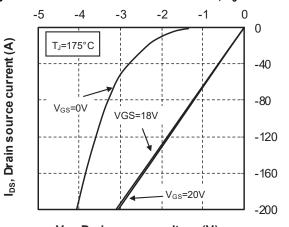
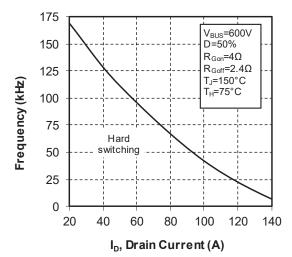


Figure 1-14. Operating Frequency vs Drain Current



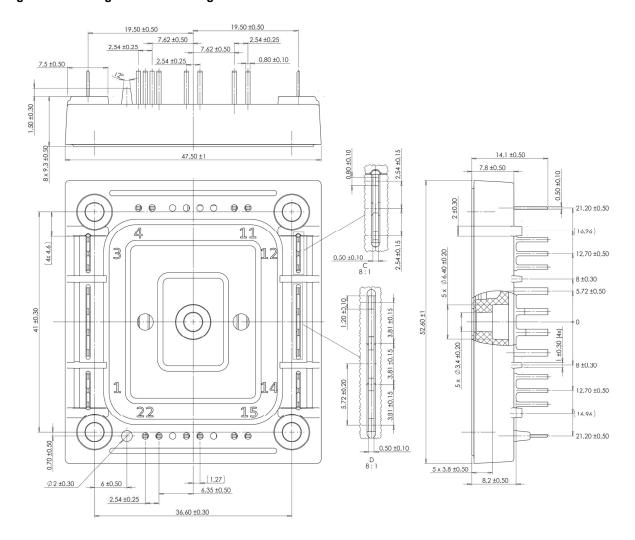
2. Package Specifications

The following section shows the package specification of the MSCSM120DDUM16TBL3NG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120DDUM16TBL3NG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See AN4306 — Mounting Instructions for Baseless Power Module for more information.

MSCSM120DDUM16TBL3NG

Revision History

3. Revision History

Revision	Date	Description
Α	06/2022	Initial Revision

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